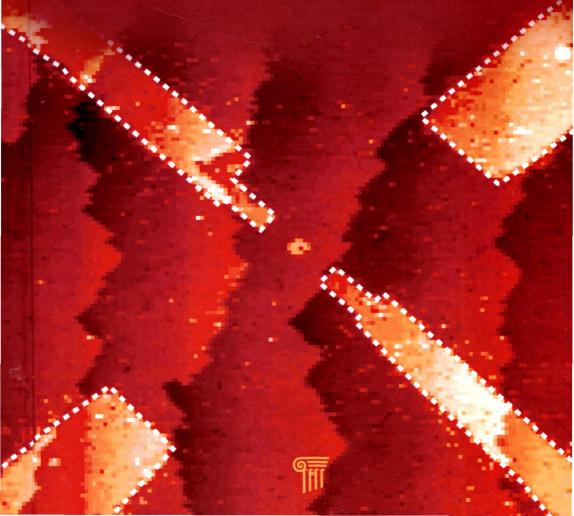


edited by Enrico Prati Takahiro Shinada



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SINGLE-ATOM NANOELECTRONICS



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